Silicon Carbide Schottky Diode

650 V, 30 A

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 144 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Automotive HEV-EV Onboard Chargers
- Automotive HEV-EV DC-DC Converters

ABSOLUTE MAXIMUM RATINGS

(T_C = 25°C, Unless otherwise specified)

| Symbol | Parar | FF- SP3065B-F085 | Unit | | |
|-----------------------------------|---|---|------|---|--|
| V _{RRM} | Peak Repetitive Rev | 650 | V | | |
| E _{AS} | Single Pulse Avalan | 144 | mJ | | |
| | Continuous Rectified @ $T_C < 135^{\circ}C$ | 30 | | | |
| I _{F, Max} | Non-Repetitive Peak Forward | $T_C = 25^{\circ}C$, 10 µs | 1100 | А | |
| | Surge Current | T _C = 150°C, 10 μs | 1000 | | |
| I _{F, SM} | Non–Repetitive Forward Surge Current | Half-Sine Pulse, t _p = 8.3 ms | 110 | A | |
| P _{tot} | Power Dissipation | $T_{C} = 25^{\circ}C$ | 197 | W | |
| | | $T_C = 150^{\circ}C$ | 33 | | |
| T _J , T _{STG} | Operating and Storac Range | –55 to +175 | °C | | |

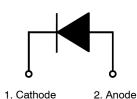
1. E_{AS} of 144 mJ is based on starting T_J = 25°C, L = 0.5 mH, I_{AS} = 24 A, V = 50 V.



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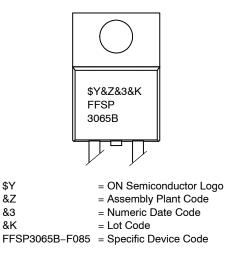
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ELECTRICAL CONNECTION





MARKING DIAGRAM



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

THERMAL CHARACTERISTICS

| Symbol | Parameter | Ratings | Unit |
|-----------------|--|---------|------|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case, Max. | 0.76 | °C/W |

PACKAGE MARKING AND ORDERING INFORMATION

| Part Number | Top Mark | Package | Packing Method | Reel Size | Tape Width | Quantity |
|----------------|-----------|---------|----------------|-----------|------------|----------|
| FFSP3065B-F085 | FFSP3065B | TO220 | Tube | N/A | N/A | 50 Units |

ELECTRICAL CHARACTERISTICS $T_C = 25^{\circ}C$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min. | Тур. | Max. | Unit |
|----------------|-------------------------|--|------|------|------|------|
| VF | Forward Voltage | I _F = 30 A, T _C = 25°C | - | 1.38 | 1.7 | V |
| | | I _F = 30 A, T _C = 125°C | - | 1.6 | 2.0 | |
| | | I _F = 30 A, T _C = 175°C | - | 1.72 | 2.4 | |
| I _R | Reverse Current | V _R = 650 V, T _C = 25°C | - | 0.5 | 40 | μA |
| | | V _R = 650 V, T _C = 125°C | - | 1.0 | 80 | |
| | | V _R = 650 V, T _C = 175°C | - | 2.0 | 160 | |
| Q _C | Total Capacitive Charge | V = 400 V | - | 74 | - | nC |
| С | Total Capacitance | V _R = 1 V, f = 100 kHz | - | 1280 | - | pF |
| | | V _R = 200 V, f = 100 kHz | - | 139 | - | |
| | | V _R = 400 V, f = 100 kHz | - | 108 | - | |

TYPICAL CHARACTERISTICS $T_J = 25^{\circ}C$ Unless Otherwise Noted

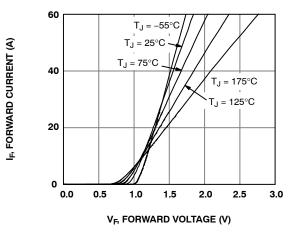


Figure 1. Forward Characteristics

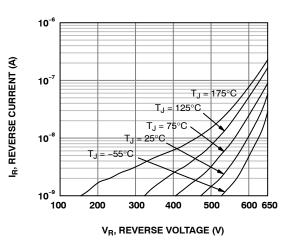
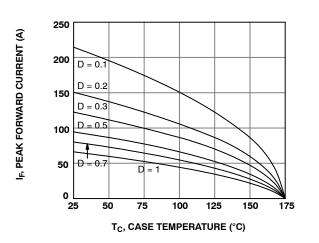
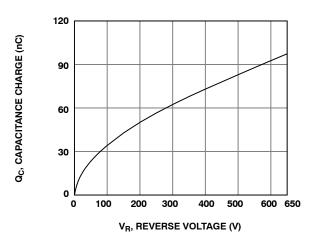


Figure 2. Reverse Characteristics









250 200 150 150 0 25 50 75 100 125 150 175 T_C, CASE TEMPERATURE (°C)

Figure 4. Power Dissipation

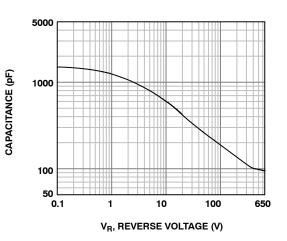
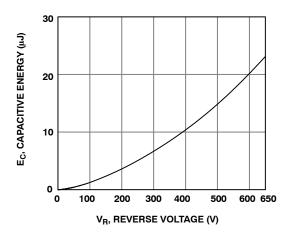
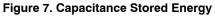
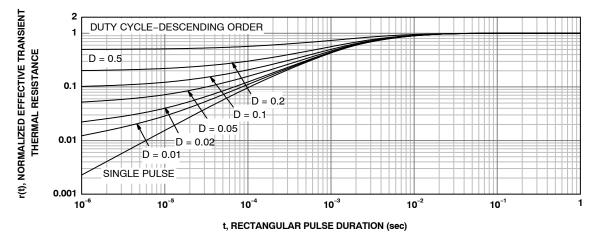


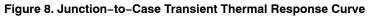
Figure 6. Capacitance vs. Reverse Voltage

TYPICAL CHARACTERISTICS T_J = 25°C Unless Otherwise Noted (continued)









TEST CIRCUIT AND WAVEFORMS

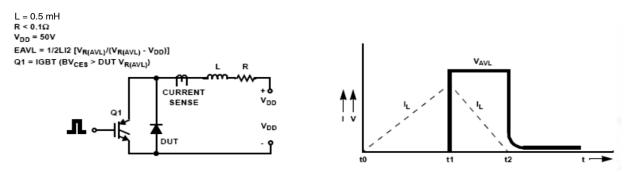
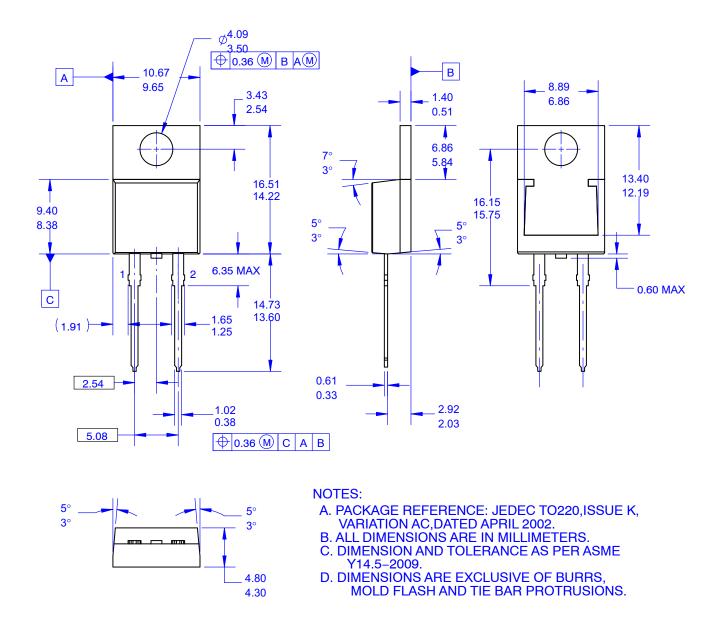


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform



TO-220-2LD CASE 340BB ISSUE O

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